

L Number	Hits	Search Text	DB	Time stamp
84	274	DFB and (semiconductor near laser) and active and clad\$5 and grating and insulat\$4 and electrode	USPAT; US-PGPUB	2003/05/02 17:08
87	32	DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode	USPAT; US-PGPUB	2003/05/02 17:09
90	28	DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode	USPAT	2003/05/02 17:36
91	25	DFB and (semiconductor near laser) and active and clad\$5 and grating and (insulat\$4 with gap) and electrode and contact	USPAT	2003/05/02 18:14
92	3	DFB and (semiconductor near laser) and active and clad\$5 and (grating with InGaAs) and (insulat\$4 with gap) and electrode and contact	USPAT	2003/05/02 18:24
93	8	DFB and (semiconductor near laser) and (grating near3 InGaAs)	USPAT	2003/05/02 18:25
-	235	(semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/31 14:04
-	172	((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:07
-	7	((semiconductor near laser) and (substrate near (layer or medium or film or region)) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near (layer or medium or film or region)) and (groove or grind or pace or rut\$ or rote) and (clad\$ near (layer or medium or film or region))) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:18
-	86	((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 11:31
-	4	((semiconductor near laser) and (substrate near (layer or medium or film or region)) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near (layer or medium or film or region)) and (groove or grind or pace or rut\$ or rote) and (clad\$ near (layer or medium or film or region))) and 372/\$ and (waveguide near (layer or film or medium or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:17
-	47	((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))) and 372/96	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:26
-	4	(semiconductor near laser) and (substrate near layer) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near layer) and (groove) and (clad\$ near layer) and 372/\$ and (waveguide near (layer or film or medium or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:29

-	4	(semiconductor near laser) and (substrate near layer) and grating and (layer near (insulat\$ or nonconductor or non adj conductor or isolat\$)) and (electrode near layer) and (groove) and (clad\$ near layer) and 372/\$ and (waveguide near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:35
-	40	((((semiconductor near laser) and substrate and grating and (insulat\$ or nonconductor or non adj conductor or isolat\$) and electrode and (groove or grind or pace or rut\$ or rote) and clad\$) and 372/\$ and (waveguide near (layer or film or medium or region))) and 372/96) and (waveguide near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 09:38
-	8	(semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote)) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 15:51
-	6	((semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote)) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)) and resonator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/01 13:26
-	2	(semiconductor near laser) and substrate and (grating same (insulat\$ or nonconductor or non adj conductor or isolat\$) with (groove or grind or pace or rut\$ or rote) same resonator) and electrode and clad\$ and 372/\$ and (waveguide near (layer or film or medium or region)) and 372/96 and (waveguide near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/02 17:07